



## DOCUMENT CHANGE REQUEST

DCR number 498 Changes required for: General

Date: 2009/04/14

Date sent: 2009/04/14

Originator: S Jeffery - ESCC

Organisation: ESA/ESTEC

Status: IMPLEMENTED

Title: Transistors Low Power RF NPN, based on type 2N3019

Number: 5201/011

Issue: 2

Other documents affected:

Page:

See attached mark-up of 5201/011 (Issue 3 - Draft B). Note that this mark-up also includes the change of DCR 447 (DCR 447 was approved 16th December 2008); it is proposed that once this DCR has been approved, DCR 447 is introduced concurrently.

Paragraph:

See attached mark-up of 5201/011 (Issue 3 - Draft B). Note that this mark-up also includes the change of DCR 447 (DCR 447 was approved 16th December 2008); it is proposed that once this DCR has been approved, DCR 447 is introduced concurrently.

Original wording:

Proposed wording:

To introduce a number of editorial and technical changes (see the attached mark-up) which are required to make this detail spec clear, complete and consistent with the standard format and content of specifications for similar Part Types. Note that this DCR replaces the withdrawn DCR 469.

Justification:

Improve the appearance, content and clarity of the spec.

Attachments:

5201011\_Issue\_3\_-\_Draft\_B.pdf, null

Modifications:

N/A

Approval signature:

A handwritten signature in black ink, appearing to read "A. G. Suter". The signature is written in a cursive style with a prominent flourish at the end.

Date signed:

2009-04-14



Pages 1 to 15

## TRANSISTORS, LOW POWER, RF, NPN

BASED ON TYPE 2N3019

ESCC Detail Specification No. 5201/011

as applicable

Issue 3 - Draft B	February 2008
-------------------	---------------



Document Custodian: European Space Agency - see <https://escies.org>

as applicable

**LEGAL DISCLAIMER AND COPYRIGHT**

European Space Agency, Copyright © 2008. All rights reserved.

The European Space Agency disclaims any liability or responsibility, to any person or entity, with respect to any loss or damage caused, or alleged to be caused, directly or indirectly by the use and application of this ESCC publication.

This publication, without the prior permission of the European Space Agency and provided that it is not used for a commercial purpose, may be:

- copied in whole, in any medium, without alteration or modification.
- copied in part, in any medium, provided that the ESCC document identification, comprising the ESCC symbol, document number and document issue, is removed.



**DOCUMENTATION CHANGE NOTICE**

(Refer to <https://escies.org> for ESCC DCR content)

DCR No.	CHANGE DESCRIPTION
<del>187, 266</del>	Specification up issued to incorporate editorial and technical changes per DCRs.

447, bld



1. GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. 5000
- (b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices

1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 The ESCC Component Number

The ESCC Component Number shall be constituted as follows:

Example: 520101103

- Detail Specification Reference: 5201011
- Component Type Variant Number: 03 (as required)

1.4.2 Component Type Variants

The component type variants applicable to this specification are as follows:

/ Terminal

Variant Number	Based on Type	Case	Lead Material and Finish	Weight max g
03	2N3019	TO-39	D2	2
04	2N3019	TO-39	D3 or D4	2

/ terminal

The lead material and finish shall be in accordance with the requirements of ESCC Basic Specification No. 23500.

1.5 MAXIMUM RATINGS

The maximum ratings shall not be exceeded at any time during use or storage.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

Characteristics	Symbols	Maximum Ratings	Unit	Remarks
Collector-Base Voltage	$V_{CBO}$	140	V	Over entire operating temperature range
Collector-Emitter Voltage	$V_{CEO}$	80	V	
Emitter-Base Voltage	$V_{EBO}$	7	V	
Collector Current	$I_C$	1	A	Continuous
Power Dissipation	$P_{tot1}$	0.8	W	At $T_{amb} \leq +25^{\circ}C$ Note 1
	$P_{tot2}$	5	W	At $T_{case} \leq +25^{\circ}C$ Note 1
Operating Temperature Range	$T_{op}$	-65 to +200	$^{\circ}C$	Note 1
Storage Temperature Range	$T_{stg}$	-65 to +200	$^{\circ}C$	Note 1
Soldering Temperature	$T_{sol}$	+260	$^{\circ}C$	Note 2

see attached

**NOTES:**

1. For  $T_{amb}$  or  $T_{case} > +25^{\circ}C$ , derate linearly to 0W at  $+200^{\circ}C$ .
1. For Variants with tin-lead plating or hot solder dip lead finish all testing performed at  $T_{amb} > +125^{\circ}C$  shall be carried out in a 100% inert atmosphere.
2. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.

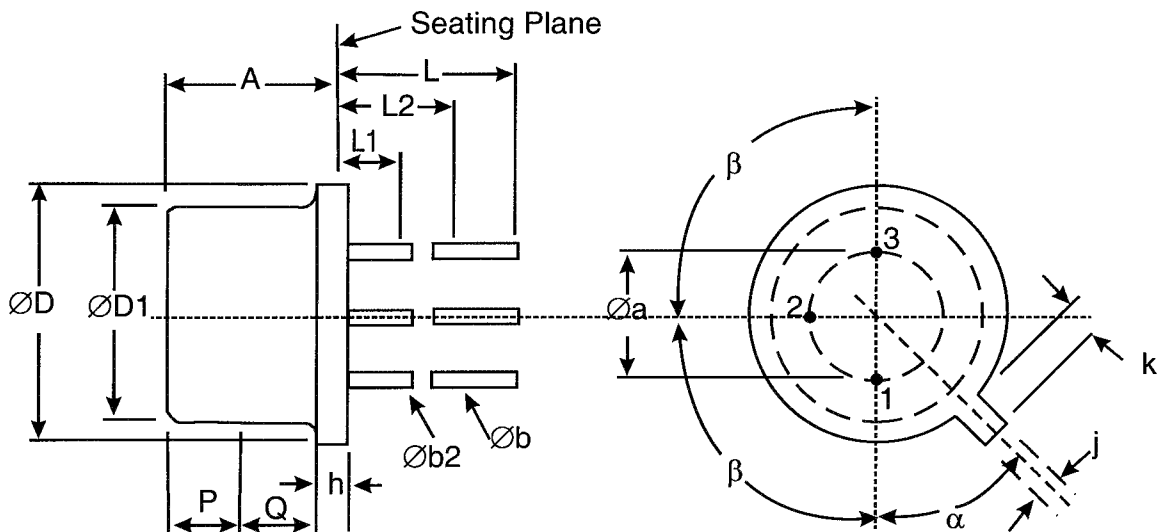
, and any handling,

make bigger

1.6

**PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION**

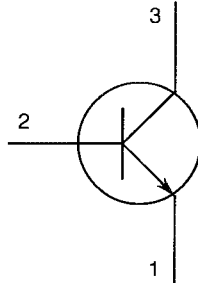
Metal Can Package (TO-39) - 3 lead



Thermal Resistance, Junction-to-Ambient	$R_{th(j-a)}$	218.8	°C/W	
Thermal Resistance, Junction-to-Case	$R_{th(j-c)}$	35	°C/W	



## 1.7 FUNCTIONAL DIAGRAM



1. Emitter.
2. Base.
3. Collector.

### NOTES:

1. The collector is internally connected to the case.

## 1.8 MATERIALS AND FINISHES

Materials and finishes shall be as follows:

- a) Case  
The case shall be hermetically sealed and have a metal body with hard glass seals.
- b) Leads / *Terminals*  
As specified in Component Type Variants.

## 2. REQUIREMENTS

### 2.1 GENERAL

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.

Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this specification.

#### 2.1.1 Deviations from the Generic Specification

##### 2.1.1.1 Deviation from Screening Tests - Chart F3

High Temperature Reverse Bias Burn-in and the subsequent Final Measurements for HTRB shall be omitted.

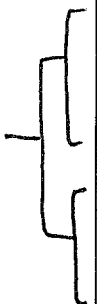
### 2.2 MARKING

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and as follows.

The information to be marked on the component shall be:

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units
				Min	Max	
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	3001	$I_C = 100\mu A$ , Bias Condition D	140	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	3011	$I_C = 30mA$ , Bias Condition D Note 1	80	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	3026	$I_E = 100\mu A$ , Bias Condition D	7	-	V
Collector-Emitter Cut-off Current	$I_{CES}$	3041	$V_{CE} = 90V$ , Bias Condition C	-	10	nA
Emitter-Base Cut-off Current	$I_{EBO}$	3061	$V_{EB} = 5V$ , Bias Condition D	-	10	nA
Collector-Emitter Saturation Voltage	$V_{CE(sat)1}$	3071	$I_C = 150mA$ $I_B = 15mA$ Note 1	-	200	mV
	$V_{CE(sat)2}$	3071	$I_C = 500mA$ $I_B = 50mA$ Note 1	-	500	mV
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	3066	Test Condition A $I_C = 150mA$ $I_B = 15mA$ Note 1	-	1.1	V
Forward-Current Transfer Ratio	$h_{FE1}$	3076	$V_{CE} = 10V$ ; $I_C = 150mA$ Note 1	100	300	-
	$h_{FE2}$	3076	$V_{CE} = 10V$ ; $I_C = 100\mu A$ Note 1	50	200	-
	$h_{FE3}$	3076	$V_{CE} = 10V$ ; $I_C = 10mA$ Note 1	90	-	-
	$h_{FE4}$	3076	$V_{CE} = 10V$ ; $I_C = 500mA$ Note 1	50	200	-
	$h_{FE5}$	3076	$V_{CE} = 10V$ ; $I_C = 1A$ Note 1	15	-	-
Magnitude of Small-Signal Short-Circuit Forward-Current Transfer Ratio	$ h_{fe} $	3306	$V_{CE} = 10V$ , $I_C = 50mA$ $f = 20MHz$ Note 2	5	20	-
Small-Signal Short-Circuit Forward-Current Transfer Ratio	$h_{fe}$	3206	$V_{CE} = 5V$ , $I_C = 1mA$ $f = 1kHz$ Note 2	80	400	-

Upper Case



Characteristics	Symbols	Limits		Units
		Min	Max	
Collector-Emitter Cut-off Current	$I_{CES}$	-	10	nA
Forward-Current Transfer Ratio 1	$h_{FE1}$	100	300	-
Collector-Emitter Saturation Voltage 2	$V_{CE(sat)2}$	-	800	mV

2.7 POWER BURN-IN CONDITIONS

Characteristics	Symbols	Conditions	Units
Ambient Temperature	$T_{amb}$	+25 (+0 -5)	°C
Power Dissipation	$P_{tot}$	800	mW
Collector-Base Voltage	$V_{CB}$	60	V

2.8 OPERATING LIFE CONDITIONS

The conditions shall be as specified for Power Burn-in.



**APPENDIX 'A'**

**AGREED DEVIATIONS FOR STMICROELECTRONICS (F)**

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS
Deviations from Room Temperature Electrical Measurements	All AC characteristics (Room Temperature Electrical Measurement Note 2) may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes AC characteristic measurements per the Detail Specification.  A summary of the pilot lot testing shall be provided if required by the Purchase Order.
Deviations from High and Low Temperatures Electrical Measurements	All characteristics specified may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes characteristic measurements at high and low temperatures per the Detail Specification.  A summary of the pilot lot testing shall be provided if required by the Purchase Order.
Deviations from Screening Tests - Chart F3	Solderability is not applicable unless specifically stipulated in the Purchase Order.

(Approved DCE 447 refers)

